

L Number	Hits	Search Text	DB	Time stamp
1	67	(sic or si adj c or silicon near carbide or wide near bandgap) near5 substrate and (trench or trenched or groove) near6 (side or wall or sidewall or bottom) near6 (doped or dopant or doping or implanted or impurities)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 09:09
2	5	("3626328" "5212104" "5488237" "5977564" "6057558").PN.	USPAT	2004/08/04 08:51
7	16	(US-6693352-\$ or US-6767783-\$ or US-5753938-\$ or US-5747831-\$ or US-4835586-\$ or US-6617653-\$ or US-6194741-\$ or US-5831288-\$).did. or (US-20040079948-\$ or US-20030127658-\$ or US-20020096687-\$ or US-20030203576-\$ or US-20030178672-\$ or US-20030227061-\$ or US-20030042538-\$).did. or (US-5753938-\$).did.	USPAT; US-PGPUB; DERWENT	2004/08/04 09:42
8	22	4835586.URPN.	USPAT	2004/08/04 09:26
9	49	5396085.URPN.	USPAT	2004/08/04 09:32
10	9	("4571815" "4587712" "4827321" "4835586" "4903189" "4961100" "5202750" "5233215" "5313082").PN.	USPAT	2004/08/04 09:39
11	63	(sic or silicon adj carbide or si adj c) near6 (sit or static adj induction adj transistor or power near2 (fet or mosfet or misfet or jfet)) and (trench or trenched or groove) near4 (impurity or doped or dopant or doping or implant or implanted or gate or gated)	USPAT; US-PGPUB; DERWENT	2004/08/04 09:44
-	336	(sic or si adj c or silicon near carbide) near5 substrate and ((source or drain) near3 (back or backside or bottom) or vertical near2 channel or gate near2 trench or gated near2 trench or gate near2 groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 08:38
-	177	(sic or si adj c or silicon near carbide) near4 substrate and gate near3 (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:26
-	17	(sic or si adj c or silicon near carbide) near4 substrate and gate near electrode near4 (bottom or beneath or below or under or underneath or lower) near3 (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 15:32
-	46	(jfet or sit or static adj induction adj transistor) and (sic or si adj c or silicon near carbide) near4 substrate and (trench or groove or recess) near5 (gate or gated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:01
-	9	("4571815" "4587712" "4827321" "4835586" "4903189" "4961100" "5202750" "5233215" "5313082").PN.	USPAT	2004/08/03 15:35
-	7	("4262296" "4941026" "4947218" "5323040" "5391895" "5396085" "5506421").PN.	USPAT	2004/08/03 15:42
-	7	5747831.URPN.	USPAT	2004/08/03 15:44
-	4	("5350699" "5859447" "6049098" "6455364").PN.	USPAT	2004/08/03 15:51
-	21	(jfet or sit or static adj induction adj transistor) and (sic or si adj c or silicon near carbide) near4 substrate and (trench or groove or recess) near3 (bottom or under or through or beneath or underneath or below) near3 (doped or channel or gate or control)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:06
-	3	(jfet or sit or static adj induction adj transistor) and (sic or si adj c or silicon near carbide) near4 substrate and (trench or groove or recess) near3 (bottom or under or through or beneath or underneath or below) near3 (doped or doping or dopant or impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:09

-	27	(sic or si adj c or silicon near carbide) near4 substrate and (trench or groove or recess) near3 (bottom or under or through or beneath or underneath or below) near3 (doped or doping or dopant or impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:14
-	107	(sit or static adj induction adj transistor) and (silicon adj carbide or sic or si adj c) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:30
-	4	("5350699" "5859447" "6049098" "6455364").PN.	USPAT	2004/08/03 16:18
-	6	("5017976" "5041881" "5166760" "5262669" "5753960" "6097046").PN.	USPAT	2004/08/03 16:19
-	2	("4866005" "5433167").PN.	USPAT	2004/08/03 16:25
-	131	(jfet) and (silicon adj carbide or sic or si adj c) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:31
-	64	(jfet) and (silicon adj carbide or sic or si adj c) near3 substrate and (trench or groove or trenched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:31
-	72	(jfet) and (silicon adj carbide or sic or si adj c) near3 substrate and (trench or groove or trenched or recess or recessed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:35
-	353	(jfet or sit or static adj induction adj transistor) and (gan or gap or cds or zno or zns or gallium adj nitride or gallium adj phosphide or cadmium adj sulfide or zinc adj oxide or zinc adj sulfide or (high or large) near2 (bandgap or gap)) near3 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:37
-	24	(jfet or sit or static adj induction adj transistor) and (gan or gap or cds or zno or zns or gallium adj nitride or gallium adj phosphide or cadmium adj sulfide or zinc adj oxide or zinc adj sulfide or (high or large) near2 (bandgap or gap)) near3 substrate and (trench or trenched or groove or recess or recessed) near3 (gate or channel or control or impurity or dopant or doped or doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 16:38